

APPLICATIONS: Snubber, IGBT & Power semiconductor direct mount

ELECTRICAL SPECIFICATIONS

Capacitance: 1 uF

Dissipation Factor: 0.0005 Max at 1000 Hz and 25°C

Temperature Coefficient: -200 PPM/°C: -100 PPM/°C, 100 PPM/°C

Ripple Current: 28 A at 100 kHz and 70°C ESR: 2.8 milliOhms (typical) at 100 kHz and 25°C Self Inductance: 1 Nanohenries maximum per mm of pitch

dvdt: 930 V/µs

Tolerance: -10 % , +10 %

Temperature Range: -40°C to +100°C

Above 85°C the rated (DC/AC) voltage must be derated at per 1.5%/2.5%°C

WVDC: 2000 Volts DC SVDC: 2600 Volts DC VAC: 700 Volts AC

applied between the terminals for 10 seconds

Terminal to Terminal Dielectric strength: 1.6 times the rated DC voltage when Terminal to case Dielectric strength: 3000 VAC when applied between the

terminals and case for 60 seconds

DC is applied for 60 seconds at 20°C

Reliability: 300 failures/billion component hours

Load Life: 100000/30000 hours at 70°C with 100% of rated voltage

Capacitance Change: ≤3% of initially measured value D.F. Change: ≤200% of maximum specified value I.R. Change: >50% of minimum specified value

Insulation Resistance (Terminal to Terminal): 3000 MINIMUM after 100 Volts Insulation resistance (Terminal to Case): N/A Megohms MINIMUM after 0 Volts

DC is applied for 0 seconds at 0

PHYSICAL DIMENSIONS

Length (L): 57.5 mm, 1.0 mm Height (H): 50 mm, +/-1.0 mm Thickness (T): 35 mm, +/-0.8 mm Lead Spacing (S): mm, +/- mm Lead Diameter (d): mm, +/-0.05 mm Lead Length (LL): mm, +/- mm



